



501.40201X00

#6/A
3/20/03

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: TADOKORO et al

Serial No.: 09/893,577

Filed: June 29, 2001

For: Fabrication Method Of Semiconductor Integrated
Circuit Device

Art Unit: 1765

Examiner: Kin Chen

AMENDMENT

RECEIVED
MAY 16 2003
TC 1700

Mail Stop Amendment
Commissioner For Patents
P.O. Box 1450
Alexandria, VA 22313-1450

May 13, 2003

Sir:

In response to the Office Action mailed January 13, 2003, please amend the
above-identified application as follows:

IN THE CLAIMS:

Please cancel claim 7 without prejudice or disclaimer, and amend the claims
remaining in the application as follows.

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- A₁ 1. (Amended) A fabrication method of a semiconductor integrated circuit device,
comprising the steps of:
(a) depositing a silicon nitride insulating film over a semiconductor substrate;